

REMARKS

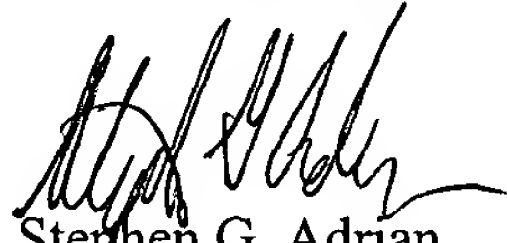
Claims 1-19 and 62-79 are pending. Claims 20-61 are cancelled, claims 1 and 3 are amended, and new claims 62-79 are added. Prompt and favorable action on the merits is earnestly solicited.

Attached hereto is a marked-up version of the changes made to the claims. The attached page is captioned "Version with markings to show changes made."

In the event that this paper is not timely filed, applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees which may be due with respect to this paper, may be charged to Deposit Account No. 01-2340.

Respectfully submitted,

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Enclosures: (1) Version with markings to show changes made

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claims 1 and 3 have been amended as follows:

1. (Amended) A semiconductor device comprising:

a semiconductor substrate having an uppermost insulating [surface] film;

[a conductive pattern disposed on the insulating surface of said semiconductor substrate,
said conductive pattern including at least one layer of metal or metal silicide;

a first insulating film made of an insulating material other than silicon nitride, and formed
to cover at least a side wall of said conductive pattern; and

a second insulating film made of silicon nitride formed to continuously cover said
conductive pattern and said first insulating film]

lamination of a first conductive film of metal or metal silicide, a first insulating film, and
a third insulating film made of silicon nitride laminated in this order from a lower side, the
lamination being formed on or above the uppermost insulating film, and having a same pattern
with a pair of side walls;

a pair of second insulating films formed on the pair of side walls of the lamination
covering at least the first conductive film, the second insulating film being made of a same
material as the first insulating film, and having a thickness smaller than that of the first insulating
film;

a pair of fourth insulating films formed on the pair of side walls of the lamination through
said second insulating films, to be contiguous to said third insulating film, the third and the
fourth insulating films collectively covering the first conductive film;

an interlevel insulating layer formed on or above said semiconductor substrate, covering said third and fourth insulating films;

an aperture formed through said interlevel insulating layer, at least partially exposing one of said fourth insulating films; and

a second conductive film filling the aperture.

3. (Amended) A semiconductor device [according to claim 2, wherein the first insulating film on the side wall of said conductive pattern is a different film from said first insulating film on the upper surface of said conductive pattern] comprising:

a semiconductor substrate having an uppermost insulating film;

lamination of a first conductive film made of metal or metal silicide, a first insulating film, and a third insulating film made of silicon nitride laminated in this order from a lower side, the lamination being formed on or above the uppermost insulating film, and having a same pattern with a pair of side walls;

a pair of second insulating films formed on the pair of side walls of the lamination covering at least the first conductive film, the second insulating film having a thickness smaller than that of the first insulating film, the first and second insulating films being made of different materials except silicon nitride;

a pair of fourth insulating films formed on the pair of side walls of the lamination through said second insulating films, to be contiguous to said third insulating film, the third and the fourth insulating films collectively covering the first conductive film;

